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Silicon Carbide (SiC) MOSFET – EliteSiC, 32 mohm, 650 V, M3S, TOLL

NTBL032N065M3S

$V_{(BR)DSS}$	$R_{DS(ON)}$ TYP	I_D MAX
650 V	32 mΩ @ 18 V	55 A

Features

- Typical $R_{DS(on)}$ = 32 mΩ @ V_{GS} = 18 V
- Ultra Low Gate Charge ($Q_{G(tot)}$ = 55 nC)
- High Speed Switching with Low Capacitance (Coss = 113 pF)
- 100% Avalanche Tested
- This Device is Halide Free and RoHS Compliant with Exemption 7a, Pb−Free 2LI (on second level interconnection)

Applications

- SMPS (Switching Mode Power Supplies)
- Solar Inverters
- UPS (Uninterruptable Power Supplies)
- Energy Storage
- EV Charging Infrastructure

S1 : Driver Source
S2 : Power Source

N−Channel MOSFET

**H−PSOF8L
CASE 100DC**

MARKING DIAGRAM

AYWWZZ
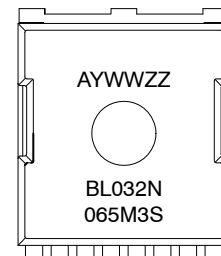
BL032N
065M3S

A	= Assembly Location
Y	= Year
WW	= Work Week
ZZ	= Assembly Lot Code
BL032N065M3S	= Specific Device Code

ORDERING INFORMATION

September, 2024 – Rev. 3

Publication Order Number:

NTBL032N065M3S/D

NTBL032N065M3S

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain−to−Source Voltage		V_{DSS}	650	V
Gate−to−Source Voltage		V_{GS}	−8/+22	V
Continuous Drain Current	T_C = 25°C	I_D	55	A
Power Dissipation		P_D	227	W
Continuous Drain Current	T_C = 100°C	I_D	39	A
Power Dissipation		P_D	113	W
Pulsed Drain Current (Note 1)	T_C = 25°C, t_p = 100 μs	I_{DM}	192	A
Continuous Source−Drain Current (Body Diode)	T_C = 25°C, V_{GS} = −3 V	I_S	33	A
	T_C = 100°C, V_{GS} = −3 V		19	
Pulsed Source−Drain Current (Body Diode) (Note 1)	T_C = 25°C, V_{GS} = −3 V, t_p = 100 μs	I_{SM}	173	A
Single Pulse Avalanche Energy (I_{LPK} = 16.7 A, L = 1 mH) (Note 2)		E_{AS}	139	mJ
Operating Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +175	°C
Lead Temperature for Soldering Purposes (1/8″ from Case for 10 s)		T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. Repetitive rating, limited by max junction temperature.
2. E_{AS} of 139 mJ is based on starting T_J = 25°C, L = 1 mH, I_{AS} = 16.7 A, V_{DD} = 100 V, V_{GS} = 18 V.

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction−to−Case (Note 3)	$R_{\theta JC}$	0.66	°C/W
Thermal Resistance, Junction−to−Ambient (Note 3)	$R_{\theta JA}$	43	°C/W

3. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Value	Unit
Operation Values of Gate−to−Source Voltage	V_{GSop}	−5...−3/+18	V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 1 mA	650			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	I_D = 1 mA, Referenced to 25°C		90		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 650 V, T_J = 25°C			10	μA
		V_{DS} = 650 V, T_J = 175°C (Note 5)			500	μA
Gate−to−Source Leakage Current	I_{GSS}	V_{GS} = −8/+22 V, V_{DS} = 0 V			±1	μA
ON CHARACTERISTICS						
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 18 V, I_D = 15 A, T_J = 25°C		32	44	mΩ
		V_{GS} = 18 V, I_D = 15 A, T_J = 175°C (Note 5)		47		
		V_{GS} = 15 V, I_D = 15 A, T_J = 25°C		41		
		V_{GS} = 15 V, I_D = 15 A, T_J = 175°C (Note 5)		52		
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 7.5 mA	2.0	2.9	4.0	V
Forward Transconductance	g_{FS}	V_{DS} = 10 V, I_D = 15 A		9.9		S
CHARGES, CAPACITANCES & GATE RESISTANCE						
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 400 V (Note 5)		1396		pF
Output Capacitance	C_{OSS}			113		
Reverse Transfer Capacitance	C_{RSS}			8.9		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = −3/18 V, V_{DD} = 400 V, I_D = 15 A (Note 5)		55		nC
Gate−to−Source Charge	Q_{GS}			15		
Gate−to−Drain Charge	Q_{GD}			14		
Gate−Resistance	R_G	f = 1 MHz		5.0		Ω
SWITCHING CHARACTERISTICS						
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = −3/18 V, V_{DD} = 400 V, I_D = 15 A, R_G = 4.7 Ω, T_J = 25°C (Notes 4, 5)		8.8		ns
Turn−Off Delay Time	$t_{d(OFF)}$			31		
Rise Time	t_r			12		
Fall Time	t_f			9		
Turn−On Switching Loss	E_{ON}			33		μJ
Turn−Off Switching Loss	E_{OFF}			16		
Total Switching Loss	E_{TOT}			49		
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = −3/18 V, V_{DD} = 400 V, I_D = 15 A, R_G = 4.7 Ω, T_J = 175°C (Notes 4, 5)		7.8		ns
Turn−Off Delay Time	$t_{d(OFF)}$			37		
Rise Time	t_r			12		
Fall Time	t_f			11		
Turn−On Switching Loss	E_{ON}			31		μJ
Turn−Off Switching Loss	E_{OFF}			25		
Total Switching Loss	E_{TOT}			56		
SOURCE−TO−DRAIN DIODE CHARACTERISTICS						
Forward Diode Voltage	V_{SD}	V_{GS} = −3 V, I_{SD} = 15 A, T_J = 25°C		4.5	6.0	V
		V_{GS} = −3 V, I_{SD} = 15 A, T_J = 175°C		4.2		

NTBL032N065M3S

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
SOURCE−TO−DRAIN DIODE CHARACTERISTICS						
Reverse Recovery Time	t_{RR}	V_{GS} = −3 V, I_S = 15 A, dI/dt = 1000 A/μs, V_{DS} = 400 V (Note 5)		15.5		ns
Charge Time	t_a			8.9		
Discharge Time	t_b			6.6		
Reverse Recovery Charge	Q_{RR}			72		nC
Reverse Recovery Energy	E_{REC}			4.6		μJ
Peak Reverse Recovery Current	I_{RRM}			9.3		A

4. EON/EOFF result is with body diode.
5. Defined by design, not subject to production test.
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NTBL032N065M3S

TYPICAL CHARACTERISTICS
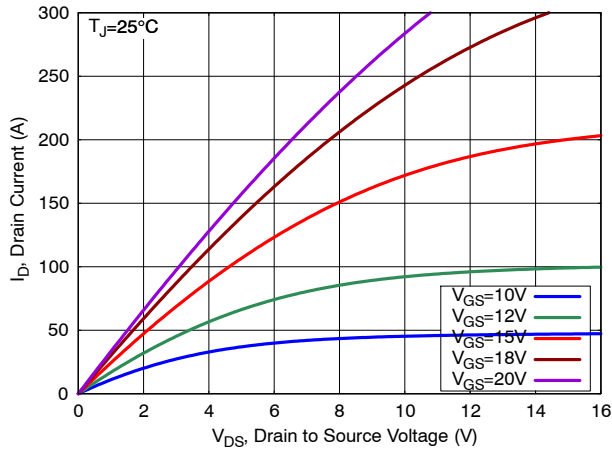
Figure 1. Output Characteristics
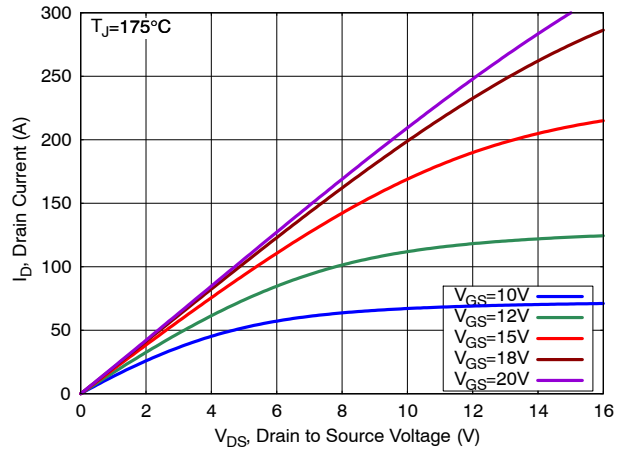
Figure 2. Output Characteristics
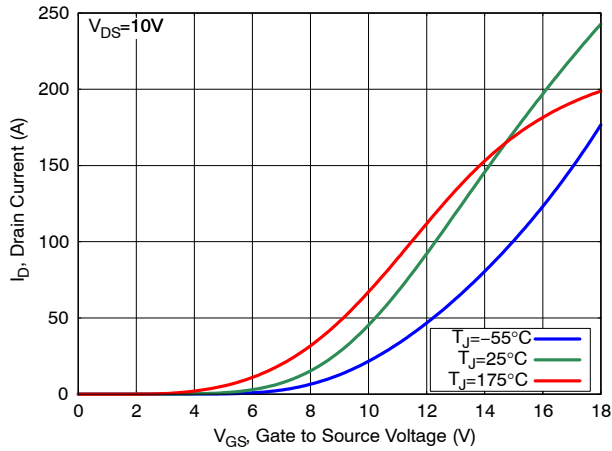
Figure 3. Transfer Characteristics
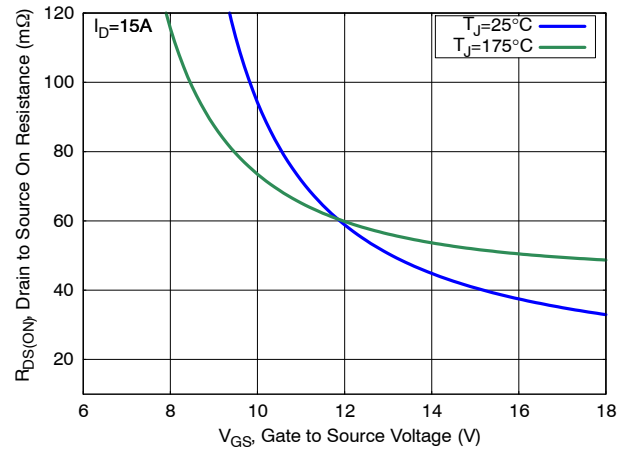
Figure 4. On−Resistance vs. Gate Voltage
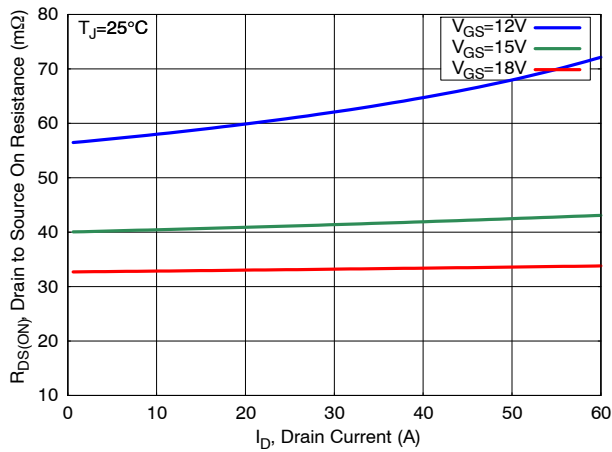
Figure 5. On−Resistance vs. Drain Current
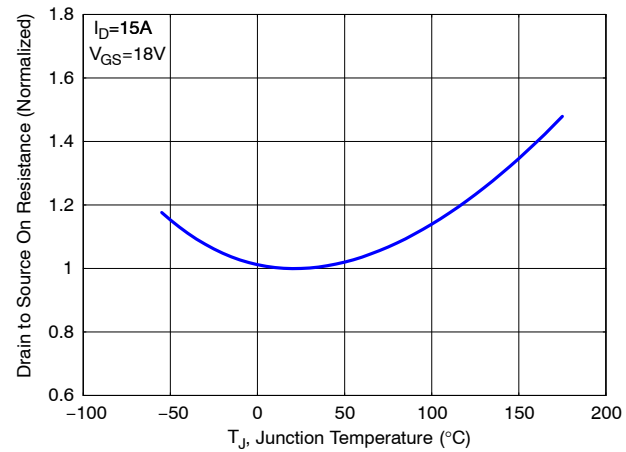
Figure 6. On−Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS
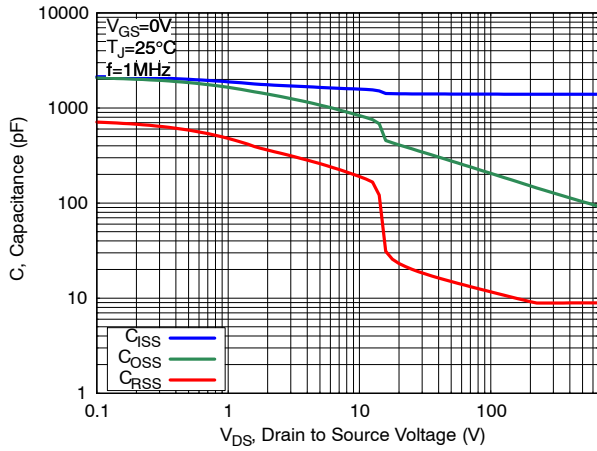
Figure 7. Capacitance Characteristics

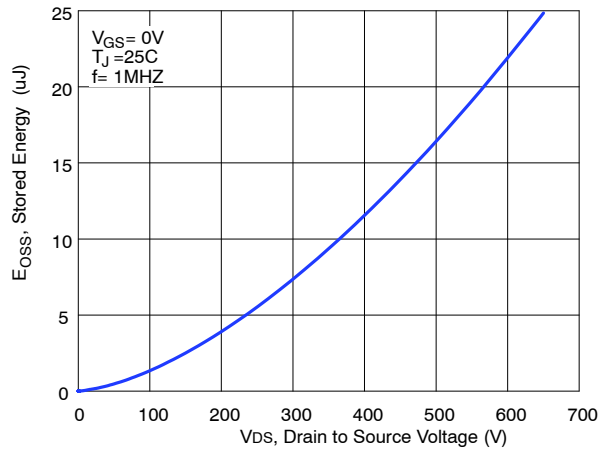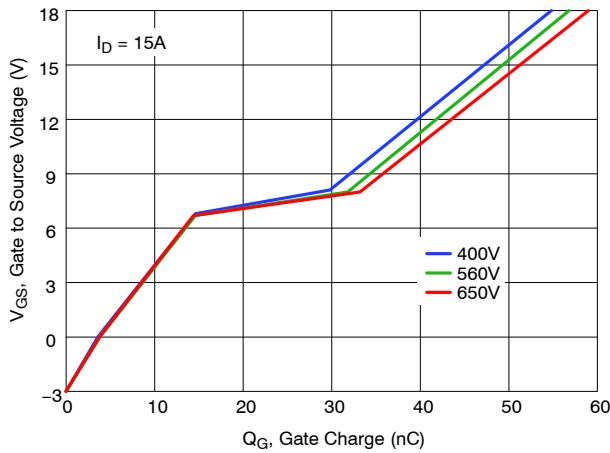

Figure 8. Stored Energy vs. Drain−to−Source Voltage
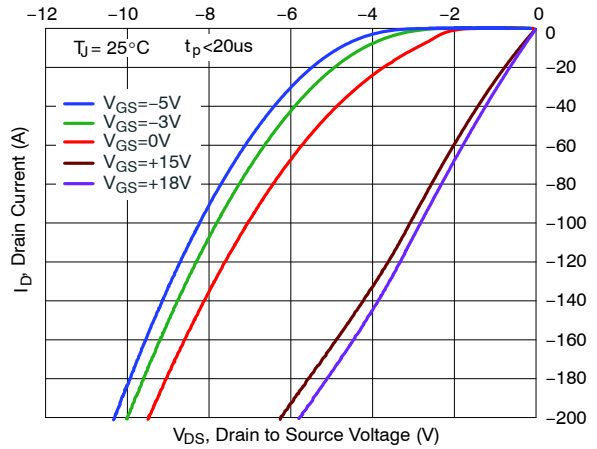

Figure 9. Gate Charge Characteristics

Figure 10. Reverse Conduction Characteristics
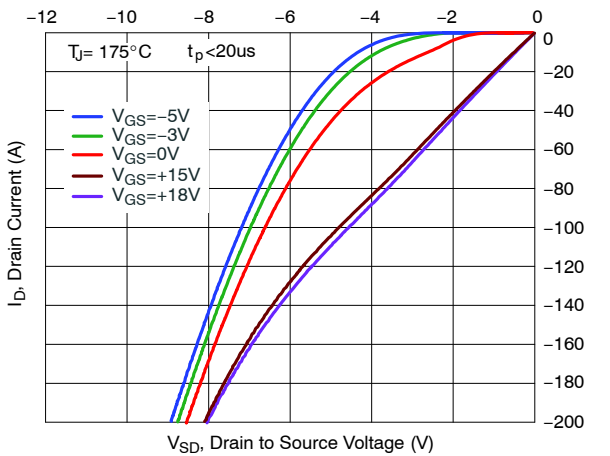
Figure 11. Reverse Conduction Characteristics
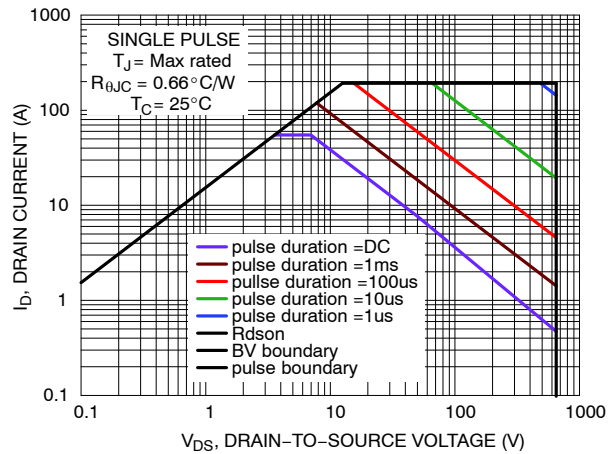
Figure 12. Safe Operating Area

TYPICAL CHARACTERISTICS

Figure 13. Avalanche Current vs. Pulse Time (UIS)
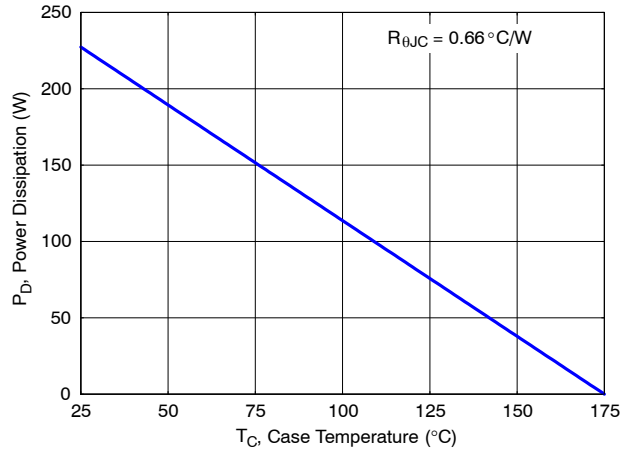
Figure 14. Maximum Power Dissipation vs. Case Temperature
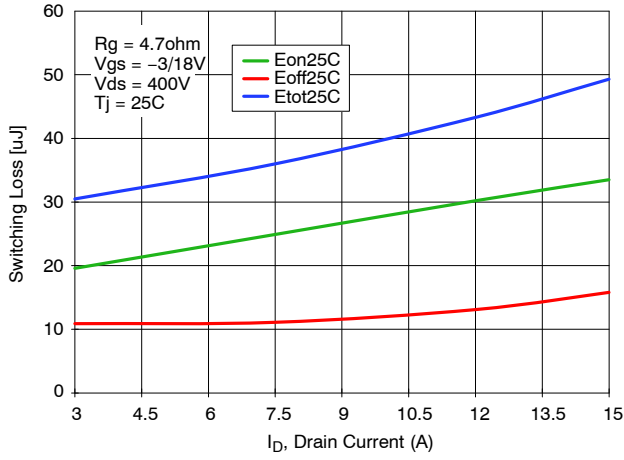
Figure 15. Inductive Switching Loss vs. Drain Current
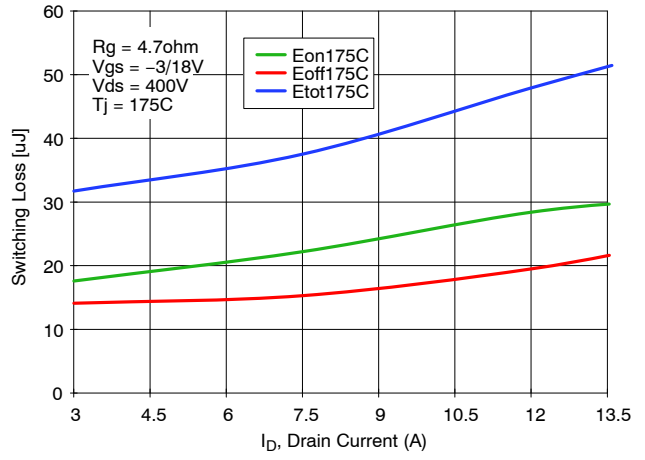
Figure 16. Inductive Switching Loss vs. Drain Current

TYPICAL CHARACTERISTICS

Figure 17. Inductive Switching Loss vs. Drain Voltage
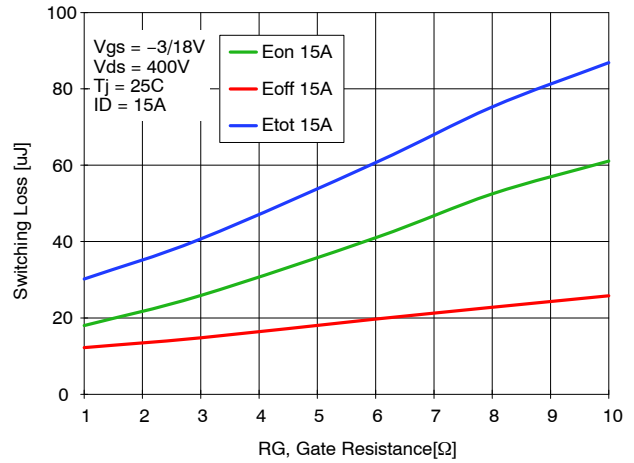
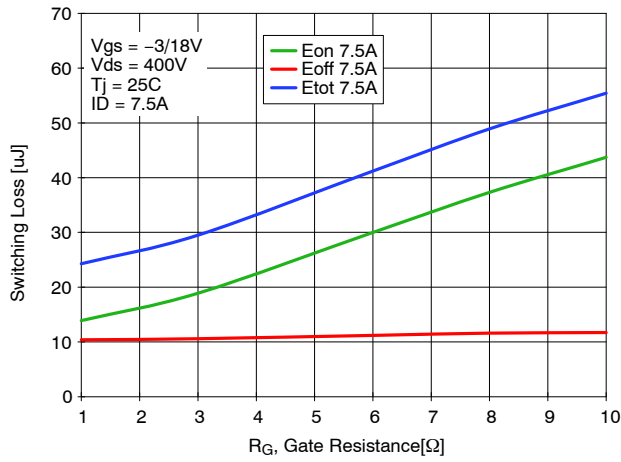

Figure 18. Inductive Switching Loss vs. Gate Resistance
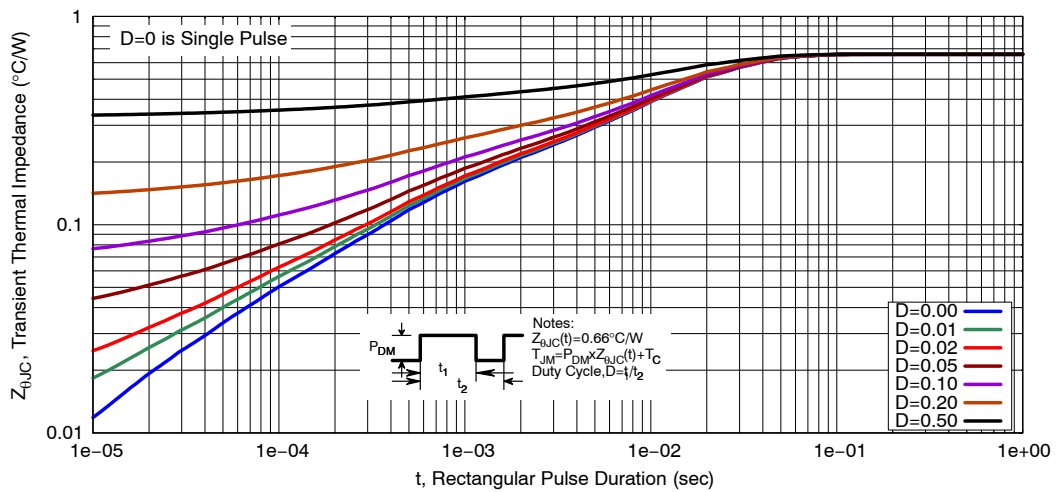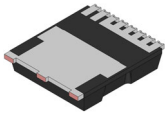

Figure 19. Inductive Switching Loss vs. Gate Resistance

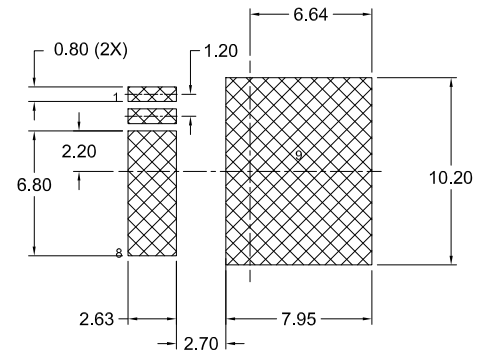**Figure 20. Thermal Response Characteristics**

DEVICE ORDERING INFORMATION

Device	Package	Shipping[†]
NTBL032N065M3S	H−PSOF8L	2000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

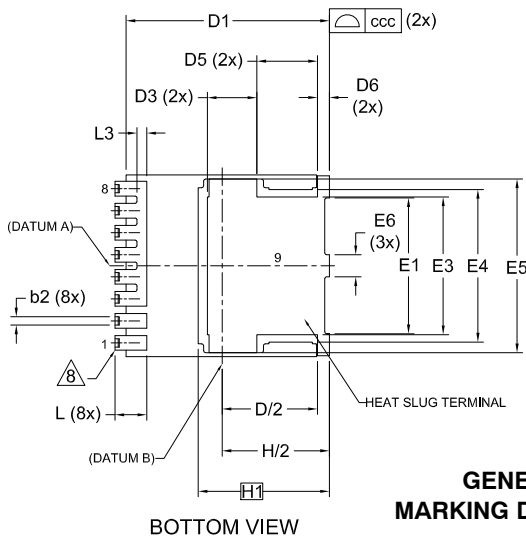**H−PSOF8L 9.90x10.38x2.30, 1.20P**
CASE 100DC
ISSUE D

DATE 30 JUL 2024

(2x) | ccc | B

D2 (2x)

TERMINAL 1 CORNER INDEX AREA △5

A

b1 E

(DATUM A)

e/2

e

b (8x)

E2

(DATUM B)

D4 (2x)

⊕ | bbb Ⓜ | C | A | B
| ddd Ⓜ | C

△6 L2 (8x) L1 △6

H

TOP VIEW

E7

E2 (2x)

Θ1

SECTION "A-A"
SCALE: 2X

(4X) Θ

c

DETAIL "B"
SCALE: 2X

// | aaa | C

A A1

SIDE VIEW

DETAIL "B"

D1

D5 (2x)

D3 (2x) D6 (2x)

L3

8

(DATUM A)

b2 (8x)

1

△8

L (8x)

D/2

H/2

(DATUM B)

H1

BOTTOM VIEW

E6 (3x)

E1 E3 E4 E5

9

HEAT SLUG TERMINAL

ccc | (2x)

0.80 (2X) 1.20

6.64

1

2.20

6.80

8

2.63 7.95

2.70

9

10.20
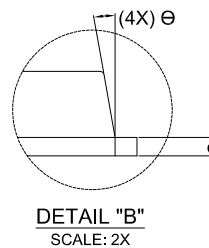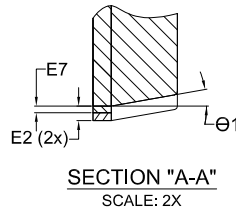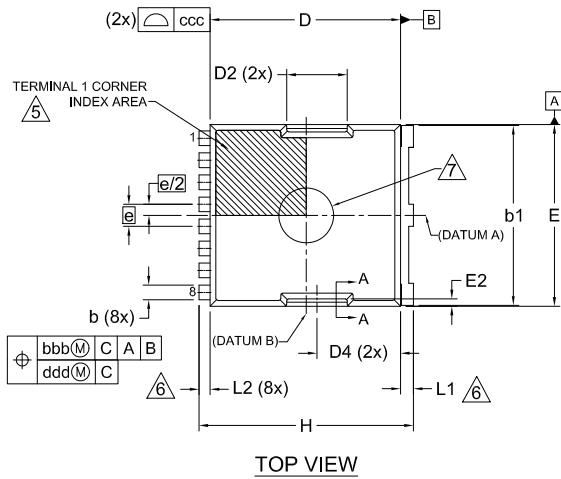
LAND PATTERN RECOMMENDATION
*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.
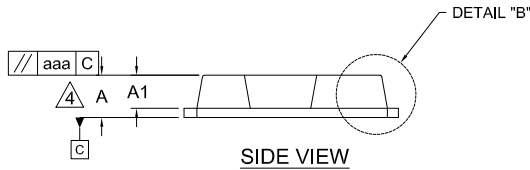
NOTES:
1. PACKAGE STANDARD REFERENCE: JEDEC MO-299, ISSUE B.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
3. "e" REPRESENTS THE TERMINAL PITCH.
4. THIS DIMENSION INCLUDES ENCAPSULATION THICKNESS "A1", AND PACKAGE BODY THICKNESS, BUT DOES NOT INCLUDE ATTACHED FEATURES, e.g.,EXTERNAL OR CHIP CAPACITORS. AN INTEGRAL HEATSLUG IS NOT CONSIDERED AS ATTACHED FEATURE.
5. A VISUAL INDEX FEATURE MUST BE LOCATED WITHIN THE HATCHED AREA.
6. DIMENSIONS b1,L1,L2 APPLY TO PLATED TERMINALS.
7. THE LOCATION AND SIZE OF EJECTOR MARKS ARE OPTIONAL.
8. THE LOCATION AND NUMBER OF FUSED LEADS ARE OPTIONAL.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
A1	1.70	1.80	1.90
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.35	0.45	0.55
c	0.40	0.50	0.60
D	10.28	10.38	10.48
D/2	5.09	5.19	5.29
D1	10.98	11.08	11.18
D2	3.20	3.30	3.40
D3	2.60	2.70	2.80
D4	4.45	4.55	4.65
D5	3.20	3.30	3.40
D6	0.55	0.65	0.75
E	9.80	9.90	10.00
E1	7.30	7.40	7.50
E2	0.30	0.40	0.50
E3	7.40	7.50	7.60
E4	8.20	8.30	8.40

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
E5	9.36	9.46	9.56
E6	1.10	1.20	1.30
E7	0.15	0.18	0.21
e	1.20 BSC		
e/2	0.60 BSC		
H	11.58	11.68	11.78
H/2	5.74	5.84	5.94
H1	7.15 BSC		
L	1.63	1.73	1.83
L1	0.60	0.70	0.80
L2	0.50	0.60	0.70
L3	0.43	0.53	0.63
Θ	10° REF		
Θ1	10° REF		
aaa	0.20		
bbb	0.25		
ccc	0.20		
ddd	0.20		
eee	0.10		

GENERIC MARKING DIAGRAM*

logo AYWWZZ

XXXXXXXX
XXXXXXXX

XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	**98AON80466G**		
DESCRIPTION:	**H−PSOF8L 9.90x10.38x2.30, 1.20P**		**PAGE 1 OF 1**

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
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ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales

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